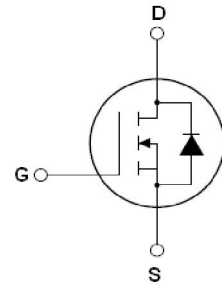


### FEATURES

- Advanced trench process technology
- avalanche energy, 100% test
- Fully characterized avalanche voltage and current
- Lead free product

**ID =84A**  
**BV=60V**  
**R<sub>DS (ON)</sub>=8mΩ**

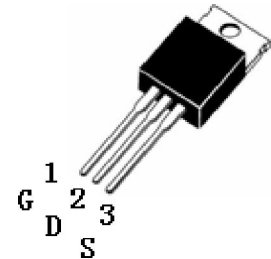


### DESCRIPTION

The SSF6008 is a new generation of high voltage and low current N-Channel enhancement mode trench power MOSFET. This new technology increases the device reliability and electrical parameter repeatability. SSF6008 is assembled in high reliability and qualified assembly house.

### APPLICATIONS

- Power switching application



SSF6008 Top View (T0-220)

### Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D@T_c=25^\circ\text{C}$	Continuous drain current, VGS@10V	84	A
$I_D@T_c=100^\circ\text{C}$	Continuous drain current, VGS@10V	76	
$I_{DM}$	Pulsed drain current ①	310	
$P_D@T_c=25^\circ\text{C}$	Power dissipation	181	W
	Linear derating factor	1.5	W/°C
$V_{GS}$	Gate-to-Source voltage	±20	V
$E_{AS}$	Single pulse avalanche energy ②	400	mJ
$E_{AR}$	Repetitive avalanche energy ①	20	mJ
dv/dt	Peak diode recovery voltage	30	v/ns
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +175	°C

### Thermal Resistance

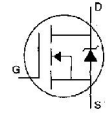
	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case	—	0.83	—	°C/W
$R_{\theta JA}$	Junction-to-ambient	—	—	62	

### Electrical Characteristics @ $T_J=25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$BV_{DSS}$	Drain-to-Source breakdown voltage	60	—	—	V	$V_{GS}=0V, I_D=250\mu\text{A}$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	5.5	8	mΩ	$V_{GS}=10V, I_D=30A$
$V_{GS(th)}$	Gate threshold voltage	2.0	—	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$
$I_{DSS}$	Drain-to-Source leakage current	—	—	2	μA	$V_{DS}=60V, V_{GS}=0V$
		—	—	10		$V_{DS}=60V, V_{GS}=0V, T_J=150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS}=20V$

	Gate-to-Source reverse leakage	—	—	-100		$V_{GS}=-20V$
$Q_g$	Total gate charge	—	90		nC	$I_D=30A, V_{GS}=10V$ $V_{DD}=30V$
$Q_{gs}$	Gate-to-Source charge	—	18	—		
$Q_{gd}$	Gate-to-Drain("Miller") charge	—	28	—		
$t_{d(on)}$	Turn-on delay time	—	18.2		nS	$V_{DD}=30V$ $I_D=2A, R_L=15\Omega$ $R_G=2.5\Omega$ $V_{GS}=10V$
$t_r$	Rise time	—	15.6			
$t_{d(off)}$	Turn-Off delay time	—	70.5			
$t_f$	Fall time	—	13.8			
$C_{iss}$	Input capacitance	—	3150		pF	$V_{GS}=0V$ $V_{DS}=25V$ $f=1.0MHZ$
$C_{oss}$	Output capacitance	—	300			
$C_{rss}$	Reverse transfer capacitance	—	240			

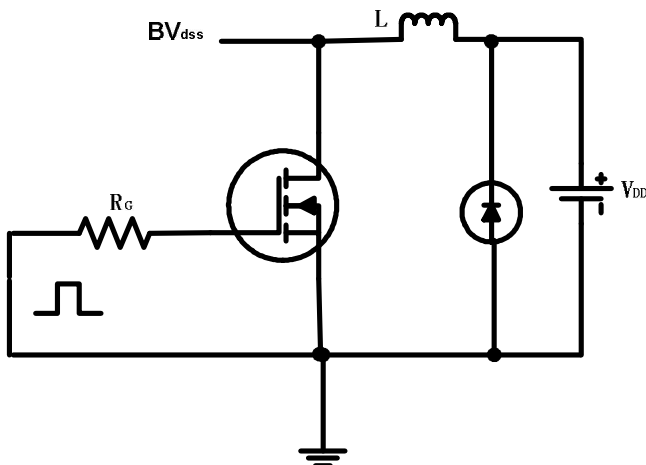
### Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$I_S$	Continuous Source Current. (Body Diode)	—	—	84	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	310		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J=25C, I_S=60A, V_{GS}=0V$ ③
$t_{rr}$	Reverse Recovery Time	—	57	—	nS	$T_J=25C, I_F=75A$
$Q_{rr}$	Reverse Recovery Charge	—	107	—	$\mu C$	$di/dt=100A/\mu s$ ③
$t_{on}$	Forward Turn-on Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

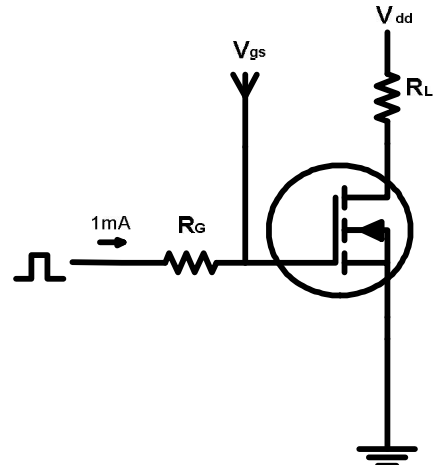
#### Notes:

- ① Repetitive rating; pulse width limited by max junction temperature.
- ② Test condition:  $L=0.3mH, V_{DD}=30V, I_D=37A$ .
- ③ Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 1.5\%$ ;  $R_G=25\Omega$  Starting  $T_J=25^\circ C$ .

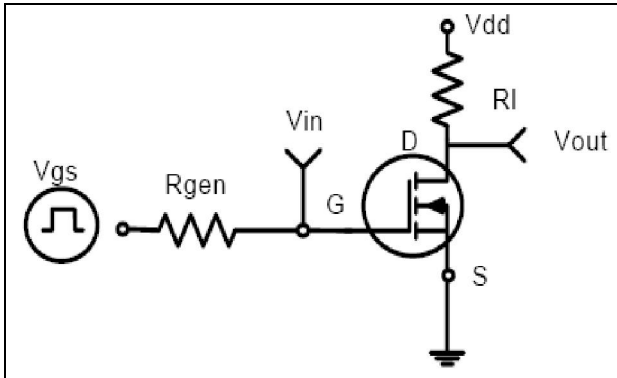
#### EAS Test Circuit



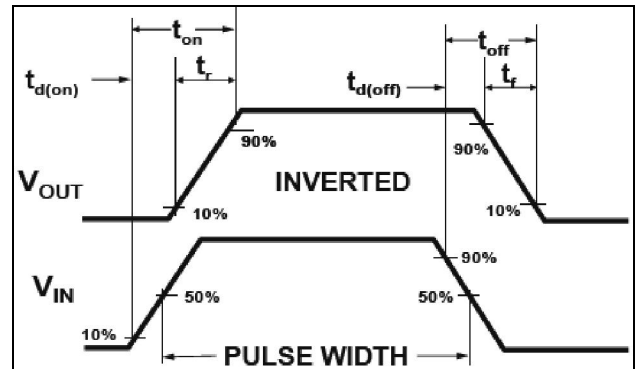
#### Gate Charge Test Circuit

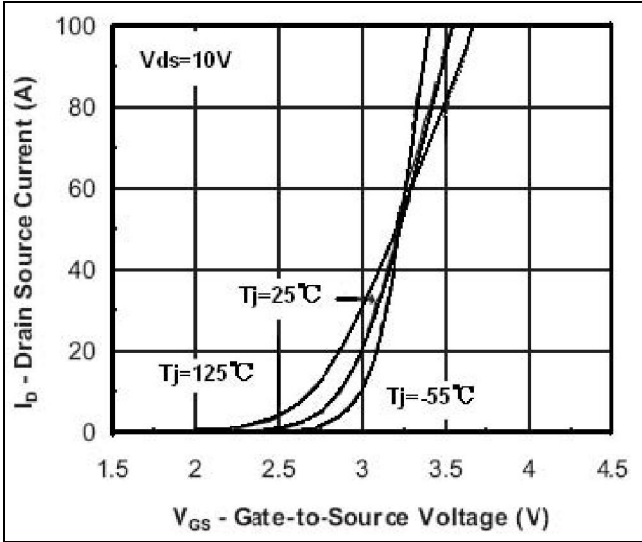


Switch Time Test Circuit

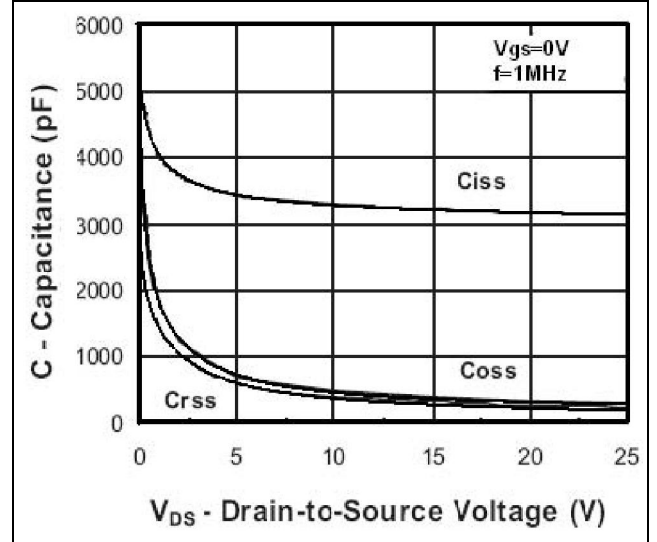


Switch Waveform

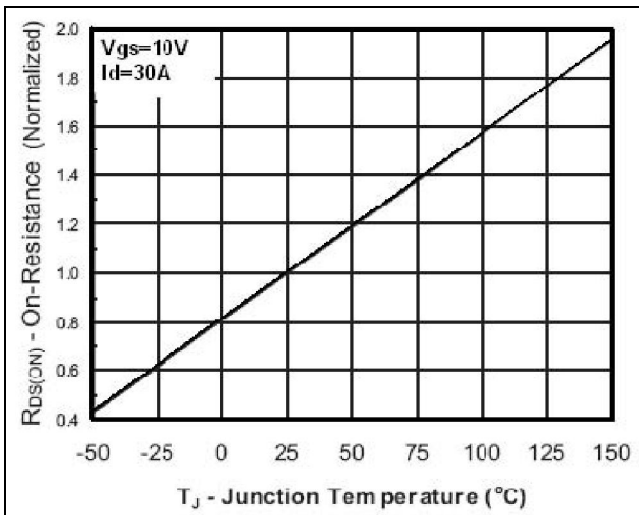




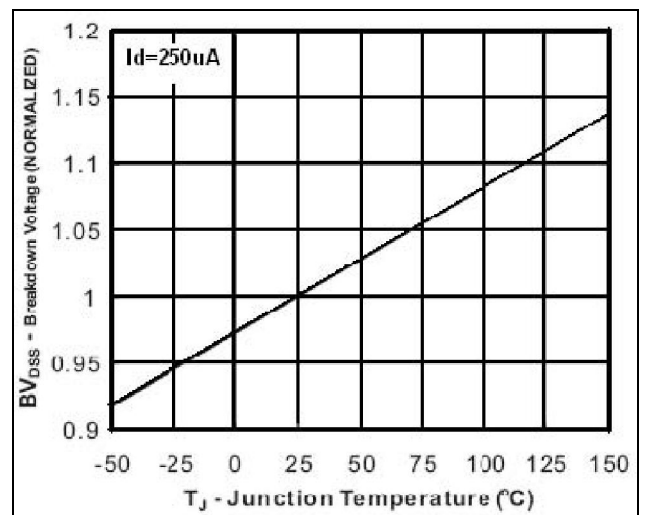
Transfer Characteristic



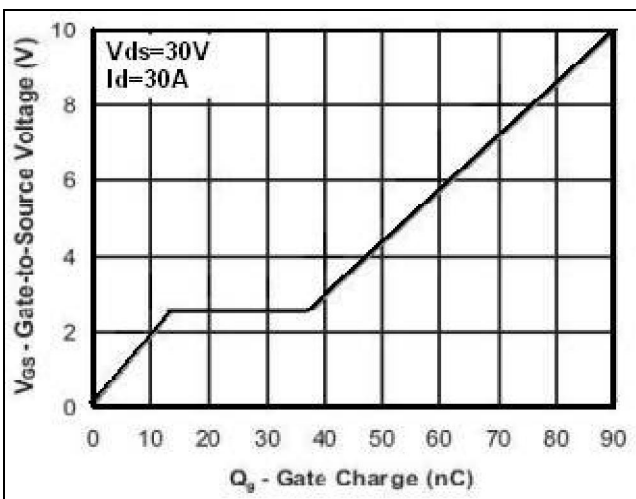
Capacitance



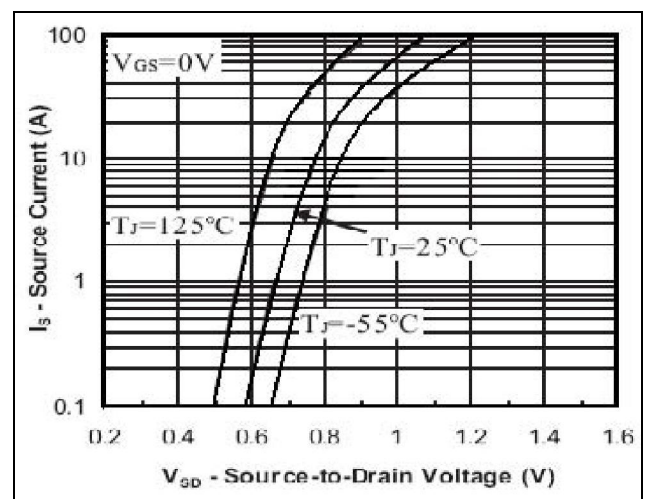
On Resistance vs. Junction Temperature



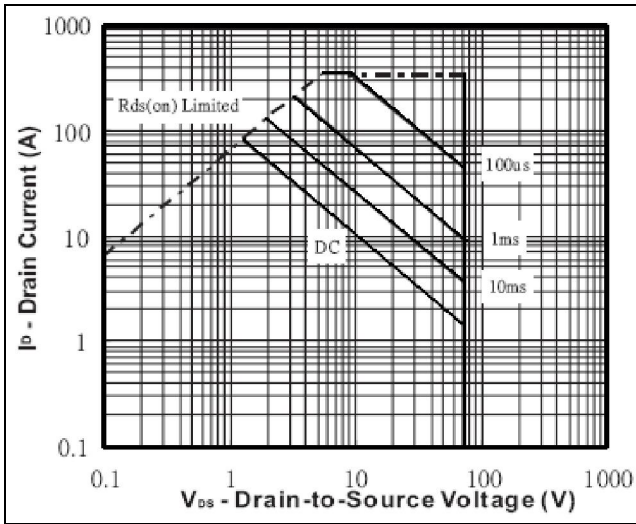
Breakdown Voltage vs. Junction Temperature



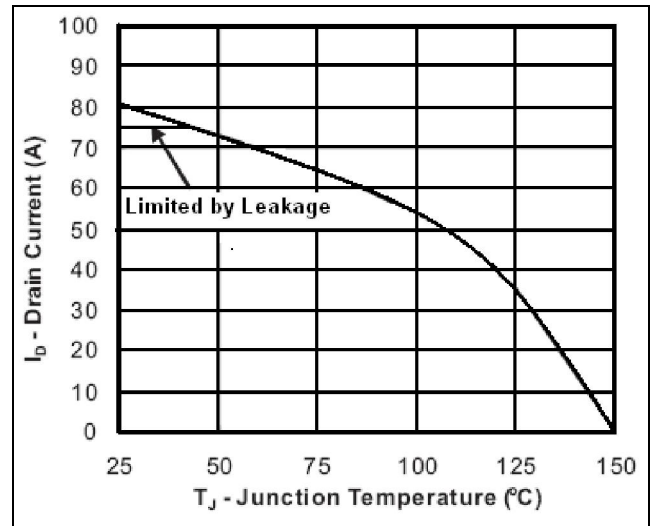
Gate Charge



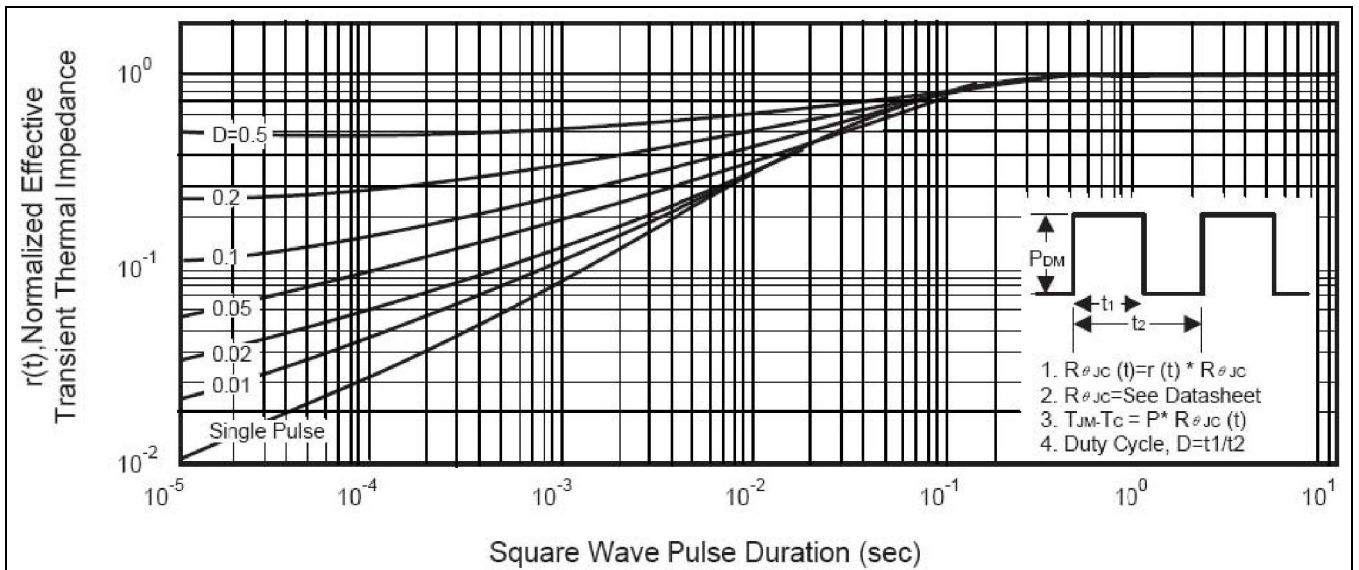
Source-Drain Diode Forward Voltage



Safe Operation Area

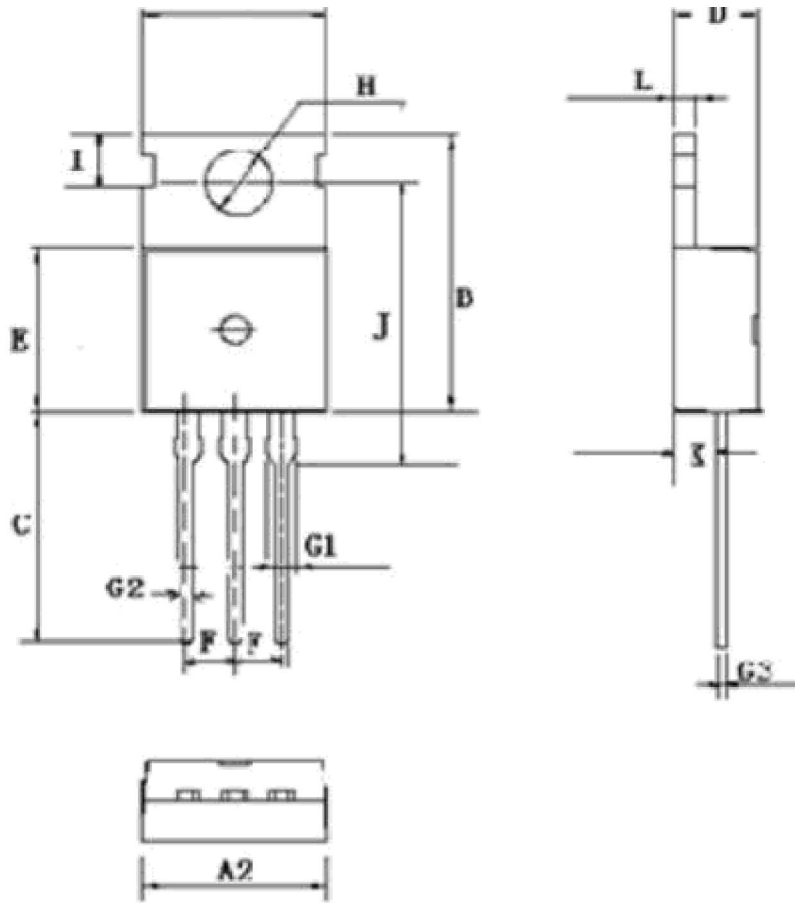


Max Drain Current vs. Junction



Transient Thermal Impedance Curve

TO-220 MECHANICAL DATA



TO-220 3L

SYMBOL	DIMENSIONS
A(mm)	9.66~10.28
A2(mm)	9.80~10.20
B(mm)	15.6~15.8
C(mm)	12.70~14.27
D(mm)	4.30~4.70
E(mm)	8.59~9.40
F(mm)	2.54 (nom)
G1(mm)	1.42~1.62
G2(mm)	0.70~0.95
G3(mm)	0.45~0.60
H(mm) dia.	3.50~3.70
I(mm)	2.7~2.9
J(mm)	15.70~16.25
K(mm)	2.20~2.90
L(mm)	1.15~1.40
M(mm)	0.5